LEDs

Part Number	Material	Max.Ratings I_F(DC) @$T_C \leq 50°C$ (mA)	Max.Ratings I_F(pulse) @$T_C \leq 50°C$ (mA)	Max.Ratings V_R (V)	Max.Ratings T_C (°C)	Max.Ratings T_{stg} (°C)	λ_P(nm) @I_F = 50mA Min.	λ_P(nm) @I_F = 50mA Max.	$\Delta\lambda$(nm) @I_F = 50mA Typ.	P_O(DC) (mW) @I_F = 50mA Min.	P_O(DC) (mW) @I_F = 50mA Typ.	P_O(pulse)* (mW) @I_F = 100mA Min.	P_O(pulse)* (mW) @I_F = 100mA Max.	θ (deg.) @I_F = 50mA Typ.	fc (MHz) @I_F = 25mA I_{RF} = 4mA$_{P-P}$		†
															Min.	Typ.	
ME1013	AlGaAs	75	120	3	−40 to +100	−55 to +125	780	880	45	1.0	1.5	2.0	3.0	40	@−1.5dB		10
															15	30	
ME1303	AlGaAs	100	150	3	−40 to +100	−55 to +125	780	875	45	1.0	1.5	2.0	3.0	40	@−1.5dB		10
															15	30	
ME1504 ME1514	AlGaAs	75	120	3	−40 to +100	−55 to +125	780	880	45	0.5	1.5	1.0	3.0	20	@−1.5dB		10
															10	30	
ME7021 ME7521	InGaAsP	120	—	2	−30 to +80	−40 to +100	@I_F = 100mA		@I_F = 100mA	@I_F = 100mA		—	—	@I_F = 100mA 20	@I_F = 70mA −1.5dB		10 11
							1260	1340	140	0.8	1.0				−	120	
ME7022 ME7522 ME7922	InGaAsP	120	—	2	−30 to +80	−40 to +100	@I_F = 100mA		@I_F = 100mA	@I_F = 100mA		—	—	@I_F = 100mA 20	@I_F = 70mA −1.5dB		10 11
							1280	1340	130	0.8	1.0				−	150	

* Pulse: duty D = 50%, f = 100kHz

Si Avalanche Photodiodes

Part Number	Material	Max.Ratings I_R(μA) @Ta ≤ 80°C	Max.Ratings I_F(mA) @Ta ≤ 80°C	Max.Ratings T_C (°C)	Max.Ratings T_{stg} (°C)	As (mm²)	$V_{(BR)R}$(V) @I_R = 100μA Min.	$V_{(BR)R}$(V) @I_R = 100μA Typ.	$V_{(BR)R}$(V) @I_R = 100μA Max.	β (%/°C) Typ.	Ct(pF) @V_R = 0.9 × $V_{(BR)R}$ Typ.	Ct(pF) @V_R = 0.9 × $V_{(BR)R}$ Max.	I_D(nA) @V_R = 50V Typ.	I_D(nA) @V_R = 50V Max.	R(A/W) @V_R = 50V λ = 800nm Min.	R(A/W) @V_R = 50V λ = 800nm Typ.	Mmax @I_{DO} = 10nA R_L = 1kΩ Typ.	f_c(GH$_z$) @M = 100 R_L = 50Ω −3dB Typ.	†
PD1002 PD1302	Si	200	10	−40 to +110	−55 to +150	3 × 10−2	100	150	200	0.12	1.5	2.0	0.3	1.0	0.4	0.45	1000	2	11
PD1005 PD1305	Si	200	10	−40 to +110	−55 to +150	2 × 10−1	100	150	200	0.12	5.0	7.0	0.3	1.0	0.4	0.45	1000	0.4	11

Si PIN Photodiodes

Part Number	Material	Max. Ratings V_R (V)	Max. Ratings I_F (mA)	Max. Ratings T_C (°C)	Max. Ratings T_{stg} (°C)	As (mm²)	I_D(nA) @V_R = 10V Typ.	I_D(nA) @V_R = 10V Max.	Ct(pF) @V_R = 5V Typ.	t_r(ns) @V_R = 5V Typ.	λ(nm)	R(A/W) @V_R = 5V λ = 650nm Min.	R(A/W) @V_R = 5V λ = 650nm Typ.	†
PD2101	Si	30	10	−40 to +110	−55 to +150	2.7 × 10−1	0.5	4	5	2	800-900	0.4	0.45	11

InGaAs Photodiodes

Part Number	Material	Max. Ratings I_R (μA)	Max. Ratings I_F (mA)	Max. Ratings T_C (°C)	Max. Ratings T_{stg} (°C)	As (mm²)	I_D(nA) @V_R = 15V	Ct(pF) @V_R = 15V	fc(MHz) @V_R = 15V R_L = 50Ω −3dB	λ (μm)	R (A/W)	†
PD7002	InGaAs	3000	2	−30 to +80	−40 to +100	7 × 10−2 (φ300μm)	300max	10max	250min	1.0-1.6	@V_R = 15V λ = 1.3μm 0.3min	11
PD7003	InGaAs	500	2	−30 to +80	−40 to +100	8 × 10−3 (φ100μm)	100max	3max	600min	1.0-1.6	@V_R = 15V λ = 1.3μm 0.6min	11
PD7004	InGaAs	3000	2	−30 to +80	−40 to +100	7 × 10−2 (φ300μm)	300max	10max	250min	1.0-1.6	@V_R = 15V λ = 1.3μm 0.6min	11
PD7005 PD7935	InGaAs	500	2	−30 to +80	−40 to +100	5 × 10−3 (φ80μm)	@V_R = 10V 1max	@V_R = 10V 1typ	@V_R = 10V 1000min	1.0-1.6	@V_R = 10V λ = 1.3μm 0.6min	11
PD7006 PD7936	InGaAs	3000	2	−30 to +80	−40 to +100	7 × 10−2 (φ300μm)	@V_R = 10V 3max	@V_R = 10V 10max	@V_R = 10V 400min	1.0-1.6	@V_R = 10V λ = 1.3μm 0.6min	11

† Column references page number of product outline drawings